

In the claims:

The following is a full listing of claims for the claims as originally filed or most recently amended. No amendments to the claims are currently presented.

1. (Previously Presented) A semiconductor device, comprising:
 - a substrate;
 - a well region, formed in the substrate;
 - a field effect transistor, formed in the well region; and
 - a diffused region, formed across the well region and the substrate for applying a back gate potential to the well region, and forming a PN diode junction together with a periphery of said diffused region, wherein the field effect transistor and the PN diode junction are connected between terminals for absorbing excess current so that an internal circuit connected to the terminals is protected.
2. (Previously Presented) The semiconductor device as set forth in claim 1, wherein a gate of the field effect transistor comprises:
 - a gate oxide film formed on a channel;
 - a protective film formed on the gate oxide film;and
 - a gate electrode comprising conductive material formed on the protective film.
3. (Original) The semiconductor device as set forth in claim 2, wherein the gate of the field effect transistor is comprised of metal.

4. (Previously Presented) The semiconductor device as set forth in claim 1, wherein the field effect transistor is a plurality of field effect transistors which are provided in the well region; and

wherein the field effect transistors share a gate structure and a drain structure.

5. (Previously Presented) The semiconductor device as set forth in claim 1, further comprising an impedance element having a larger impedance than the impedance of the field effect transistor and a diode forming the PN diode junction in a case that the field effect transistor and the diode are turned on.

wherein the impedance element is arranged between the internal circuit and at least one of the field effect transistor and the diode.

6. (Previously Presented) The semiconductor device as set forth in claim 1, further comprising a second diffused region connected to the diffused region so that the PN diode junction is formed with the diffused region.

7. (Previously Presented) A semiconductor device, comprising:

an internal circuit, connected to a plurality of terminals; and

a protection circuit, connected between the terminals for protecting the internal circuit,

wherein the protection circuit includes:

a first element, having a response to a potential difference pulse between terminals of said first element of a rising edge of current equivalent to that of a diode; and

a second element, having an impedance equivalent to that of a transistor after the rising edge of current response of said first element.

8. (Previously Presented) The semiconductor device as set forth in claim 7, wherein said first element and said second element of said protection circuit are connected in parallel.